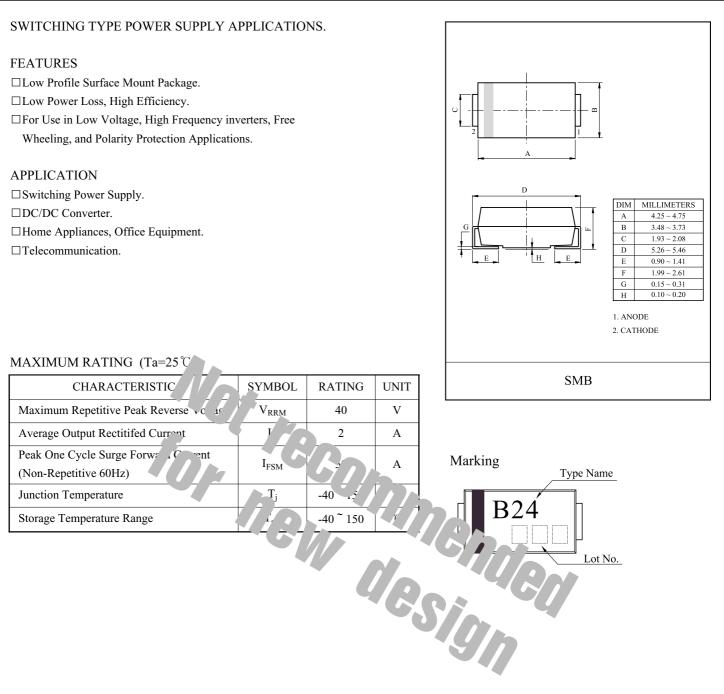


SEMICONDUCTOR TECHNICAL DATA

SMBB24

SCHOTTKY BARRIER TYPE DIODE

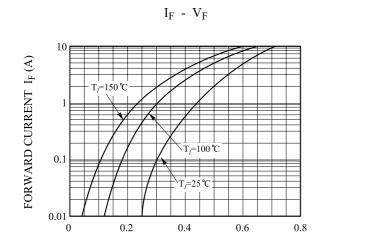


ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V _{FM}	I _{FM} =2.0A	-	-	0.5	V
Repetitive Peak Reverse Current	I _{RRM}	V _{RRM} =Rated, Tj=25 °C	-	-	0.1	mA
		V _{RRM} =Rated, Tj=100℃	-	-	10	mA
Total Capacitance	CT	V _R =4V, f=1MHz	-	-	200	pF
Thermal Resistance	R _{th(j-1)}	Junction to lead	-	-	15	°C/W

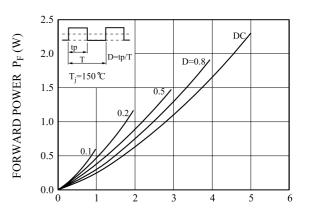
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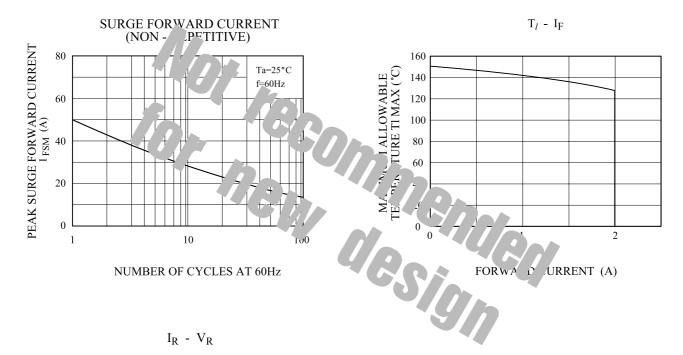


FORWARD VOLTAGE V_F(V)

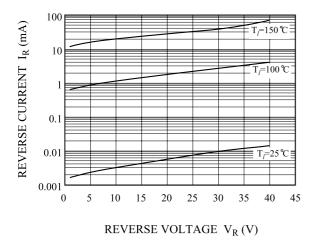
 P_F - I_F



FORWARD CURRENT I_F (A)







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